

JTDB 25

25 Watts, 36 Volts, Pulsed Avionics 960 - 1215 MHz

GENERAL DESCRIPTION

The JTDB 25 is a high power COMMON BASE bipolar transistor. It is designed for pulsed systems in the frequency band 960-1215 MHz. The device has gold thin-film metallization and diffused ballasting for proven highest MTTF. The transistor includes input and output prematch for broadband capability. Low thermal resistance package reduces junction temperature, extends life.

ABSOLUTE MAXIMUM RATINGS

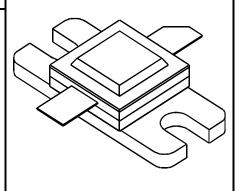
Maximum Power Dissipation @ 25°C² 97 Watts

Maximum Voltage and Current

BVcesCollector to Base Voltage55 VoltsBVeboEmitter to Base Voltage3.5 VoltsIcCollector Current5.0 Amps

Maximum Temperatures

Storage Temperature $-65 \text{ to} + 200^{\circ}\text{C}$ Operating Junction Temperature $+200^{\circ}\text{C}$ CASE OUTLINE 55AW, STYLE 1



ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$\begin{array}{c} \textbf{Pout} \\ \textbf{Pin} \\ \textbf{Pg} \\ \eta_c \\ \textbf{VSWR} \end{array}$	Power Out Power Input Power Gain Collector Efficiency Load Mismatch Tolerance	$F = 960-1215 \text{ MHz}$ $Vcc = 36 \text{ Volts}$ $PW = 10 \mu\text{sec}$ $DF = 40\%$ $F = 1090 \text{ MHz}$	25 7.0	7.5 40	5.0 5:1	Watts Watts dB %

BVebo	Emitter to Base Breakdown	Ie = 5 mA	3.5		Volts
BVces	Collector to Emitter Breakdown	Ic = 10 mA	55		Volts
$\mathbf{h}_{\mathbf{FE}}$	DC - Current Gain	Ic = 500 mA, Vce = 5 V	10		
$\Theta \mathbf{j} \mathbf{c}^2$	Thermal Resistance			1.8	°C/W

Note 1: At rated output power and pulse conditions

2: At rated pulse conditions

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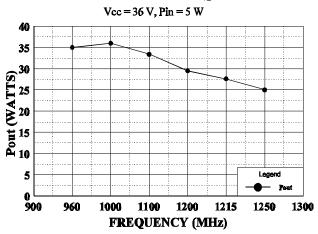
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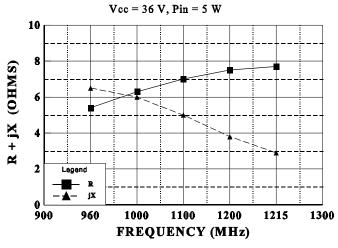
JTDB25

All Data shown is for operation under the rated pulse conditions.

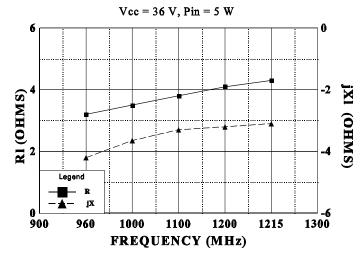
POWER OUTPUT vs FREQUENCY



SERIES INPUT IMPEDANCE vs FREQUENCY



SERIES LOAD IMPEDANCE vs FREQUENCY



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